



N-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | |
|---------------------|-----------------------------------|--------------------|-----------------------|--|--|--|
| V _{DS} (V) | $R_{DS(on)}(\Omega)$ | I _D (A) | Q _g (Typ.) | | | |
| 30 | 0.004 at V _{GS} = 10 V | 28 | 36 | | | |
| | 0.0048 at V _{GS} = 4.5 V | 25 | 30 | | | |

PowerPAK SO-8 6.15 mm 5.15 mm 2 3 4

Ordering Information: Si7636DP-T1-E3 (Lead (Pb)-free)

Bottom View

Si7636DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

Halogen-free According to IEC 61249-2-21
Available



 Ultra-Low On-Resistance Using High Density TrenchFET[®] Gen II Power MOSFET Technology COMPLIANT

Q_a Optimized

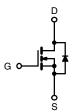
New Low Thermal Resistance PowerPAK[®]
 Package with Low 1.07 mm Profile

100 % R_q Tested

HALOGEN FREE

APPLICATIONS

- · Low-Side DC/DC Conversion
 - Notebook
 - Server
 - Workstation
- Synchronous Rectifier, POL



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS | T _A = 25 °C, unle | ss otherwise r | noted | | |
|---|------------------------------|-----------------------------------|--------------|------|----|
| Parameter | Symbol | 10 s | Steady State | Unit | |
| Drain-Source Voltage | V_{DS} | 30 | | V | |
| Gate-Source Voltage | V_{GS} | ± | V | | |
| Continuous Drain Current (T _J = 150 °C) ^a | T _A = 25 °C | I _D | 28 | 17 | |
| Continuous Drain Current (1 J = 150 °C) | T _A = 70 °C | | 22 | 13 | |
| Pulsed Drain Current (10 µs Pulse Width) | I _{DM} | 60 | | Α | |
| Continuous Source Current (Diode Conduction) ^a | I _S | 4.3 | 1.7 | | |
| Avalanche Current L = 0.1 mH | | I _{AS} | 50 | | |
| Mariana Damar Dissipation | T _A = 25 °C | P _D | 5.2 | 1.9 | W |
| Maximum Power Dissipation ^a | T _A = 70 °C | י ט | 3.3 | 1.2 | VV |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | | °C |
| Soldering Recommendations (Peak Temperature) ^{b,c} | | | 260 | | C |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| Manimum Investiga to Austriant | t ≤ 10 s | R _{thJA} | 19 | 24 | °C/W | |
| Maximum Junction-to-Ambient ^a | Steady State | ' 'thJA | 52 | 65 | | |
| Maximum Junction-to-Case (Drain) | Steady State | R _{thJC} | 1.3 | 1.8 | | |

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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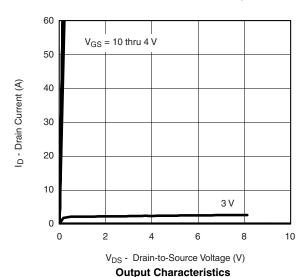
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
|---|-----------------------|--|------|--------|--------|------|--|
| Static | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 1.0 | | 3.0 | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| Zava Cata Valtaga Drain Current | 1 | V _{DS} = 30 V, V _{GS} = 0 V | | | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$ | | | 5 | μΑ | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 30 | | | Α | |
| | В | V _{GS} = 10 V, I _D = 25 A | | 0.0033 | 0.004 | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} – | $V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A}$ | | 0.004 | 0.0048 | Ω | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = 15 V, I _D = 25 A | | 110 | | S | |
| Diode Forward Voltage ^a | V_{SD} | I _S = 2.9 A, V _{GS} = 0 V | | 0.72 | 1.1 | ٧ | |
| Dynamic ^b | | | | • | | | |
| Input Capacitance | C _{iss} | | | 5600 | | | |
| Output Capacitance | C _{oss} | $V_{DS} = 15 \text{ V}, V_{DS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 860 | | pF | |
| Reverse Transfer Capacitance | C _{rss} | | | 415 | | | |
| Total Gate Charge | Q_g | | | 36 | 50 | | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 20 \text{ A}$ | | 18 | | nC | |
| Gate-Drain Charge | Q_{gd} | | | 10 | | | |
| Gate Resistance | R_g | | 0.6 | 1.3 | 2.0 | Ω | |
| Turn-On Delay Time | t _{d(on)} | | | 24 | 35 | | |
| Rise Time | t _r | V_{DD} = 15 V, R_L = 15 Ω | | 16 | 25 | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D\cong 1$ A, V_{GEN} = 10 V, R_g = 6 Ω | | 90 | 140 | ns | |
| Fall Time | t _f | | | 32 | 50 | | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = 2.9 A, dI/dt = 100 A/μs | | 45 | 70 | | |

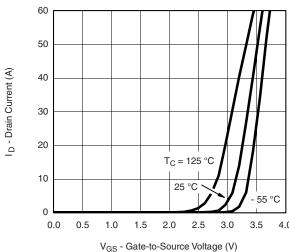
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Transfer Characteristics



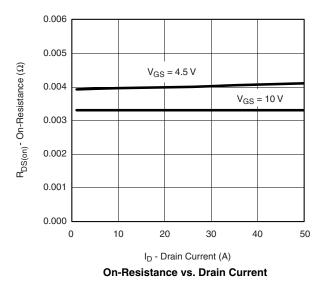


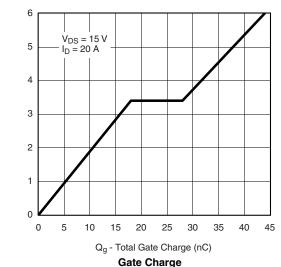


V_{GS} - Gate-to-Source Voltage (V)

Is - Source Current (A)

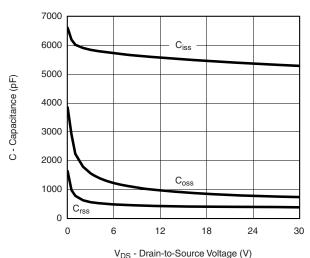
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





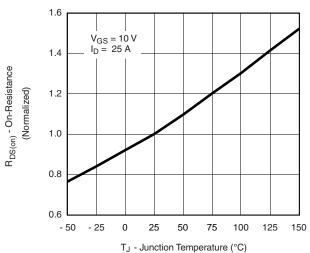
10 T_J = 150 °C T_J = 25 °C T

Source-Drain Diode Forward Voltage

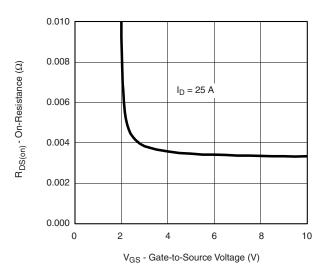


VDS - Diam-to-Source voltage (V)

Capacitance



On-Resistance vs. Junction Temperature

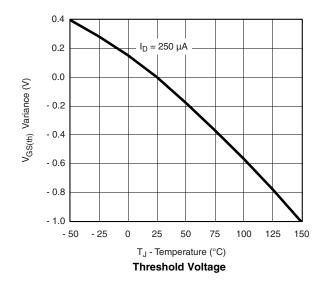


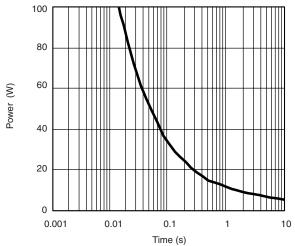
On-Resistance vs. Gate-to-Source Voltage

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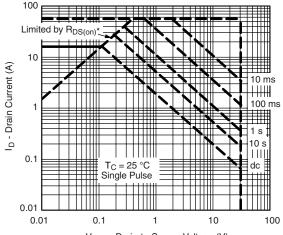
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



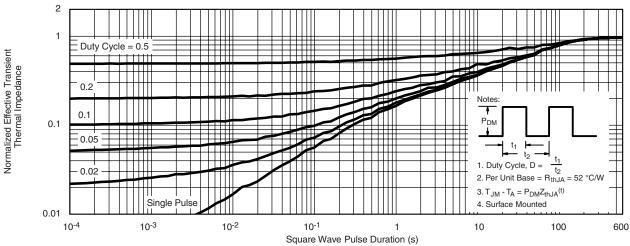


Single Pulse Power, Junction-to-Ambient



 $V_{DS} \ - \ Drain-to-Source \ Voltage \ (V)$ * $V_{GS} > minimum \ V_{GS}$ at which $R_{DS(on)}$ is specified

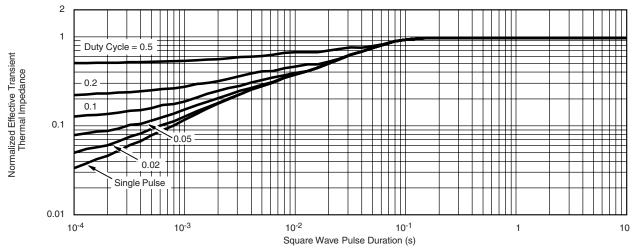
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



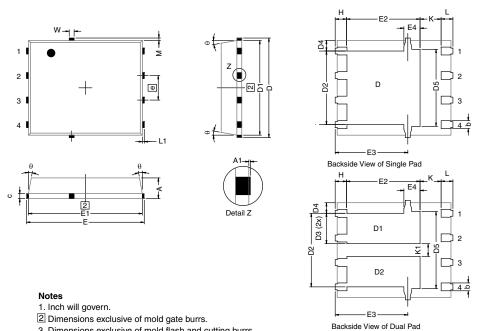
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72768.



DWG: 5881

PowerPAK® SO-8, (Single/Dual)



| | 3. Dimensions exclusive | of mold flash and cuttin | g burrs. | | | | | |
|------|-------------------------|--------------------------|----------|-------|--------|-------|--|--|
| | | MILLIMETERS | | | INCHES | | | |
| DIM. | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | | |
| A | 0.97 | 1.04 | 1.12 | 0.038 | 0.041 | 0.044 | | |
| A1 | | - | 0.05 | 0 | - | 0.002 | | |
| b | 0.33 | 0.41 | 0.51 | 0.013 | 0.016 | 0.020 | | |
| С | 0.23 | 0.28 | 0.33 | 0.009 | 0.011 | 0.013 | | |
| D | 5.05 | 5.15 | 5.26 | 0.199 | 0.203 | 0.207 | | |
| | 4.00 | 4.00 | F 00 | 0.400 | 0.400 | 0.407 | | |

| Α | 0.97 | 1.04 | 1.12 | 0.038 | 0.041 | 0.044 | | |
|--------------------------|------------|-----------|------|------------|-------------|-------|--|--|
| A1 | | - | 0.05 | 0 | - | 0.002 | | |
| b | 0.33 | 0.41 | 0.51 | 0.013 | 0.016 | 0.020 | | |
| С | 0.23 | 0.28 | 0.33 | 0.009 | 0.011 | 0.013 | | |
| D | 5.05 | 5.15 | 5.26 | 0.199 | 0.203 | 0.207 | | |
| D1 | 4.80 | 4.90 | 5.00 | 0.189 | 0.193 | 0.197 | | |
| D2 | 3.56 | 3.76 | 3.91 | 0.140 | 0.148 | 0.154 | | |
| D3 | 1.32 | 1.50 | 1.68 | 0.052 | 0.059 | 0.066 | | |
| D4 | | 0.57 typ. | | | 0.0225 typ. | | | |
| D5 | | 3.98 typ. | | | 0.157 typ. | | | |
| E | 6.05 | 6.15 | 6.25 | 0.238 | 0.242 | 0.246 | | |
| E1 | 5.79 | 5.89 | 5.99 | 0.228 | 0.232 | 0.236 | | |
| E2 (for AL product) | 3.30 | 3.48 | 3.66 | 0.130 | 0.137 | 0.144 | | |
| E2 (for other product) | 3.48 | 3.66 | 3.84 | 0.137 | 0.144 | 0.151 | | |
| E3 | 3.68 | 3.78 | 3.91 | 0.145 | 0.149 | 0.154 | | |
| E4 (for AL product) | | 0.58 typ. | | | 0.023 typ. | | | |
| E4 (for other product) | | 0.75 typ. | | | 0.030 typ. | | | |
| е | | 1.27 BSC | | 0.050 BSC | | | | |
| K (for AL product) | | 1.45 typ. | | 0.057 typ. | | | | |
| K (for other product) | | 1.27 typ. | | 0.050 typ. | | | | |
| K1 | 0.56 | - | = | 0.022 | - | = | | |
| Н | 0.51 | 0.61 | 0.71 | 0.020 | 0.024 | 0.028 | | |
| L | 0.51 | 0.61 | 0.71 | 0.020 | 0.024 | 0.028 | | |
| L1 | 0.06 | 0.13 | 0.20 | 0.002 | 0.005 | 0.008 | | |
| θ | 0° | - | 12° | 0° | - | 12° | | |
| W | 0.15 | 0.25 | 0.36 | 0.006 | 0.010 | 0.014 | | |
| M | 0.125 typ. | | | 0.005 typ. | | | | |
| ECN: C13-0702-Rev. K, 20 |)-May-13 | | | • | | | | |

Revison: 20-May-13 Document Number: 71655



RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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Revision: 02-Oct-12 Document Number: 91000